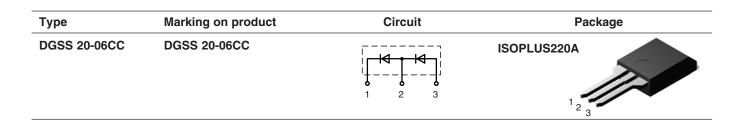


## **Gallium Arsenide Schottky Rectifier**

Second generation ISOPLUS220<sup>™</sup> Electrically Isolated Back Surface

Preliminary Data

 $V_{\text{RRM}}$  = 600 V (2x300V)  $I_{\text{DC}}$  = 38 A  $C_{\text{Junction}}$  = 16 pF



Diode					
Symbol	Conditions	Maximum Rat			
V <sub>RRM/RSM</sub> V <sub>RRM/RSM</sub>	(between terminal 1 and 3)	600 300	V V		
I <sub>FAV</sub> I <sub>FAV</sub>	$T_c = 25^{\circ}C; DC$ $T_c = 90^{\circ}C; DC$	38 23	A A		
I <sub>FSM</sub>	$T_{v_J} = 45^{\circ}C; t_p = 10 \text{ ms} (50 \text{ Hz}), \text{ sine}$	110	Α		
P <sub>tot</sub>	$T_c = 25^{\circ}C$	45	W		

Symbol				tic Values max.	
V <sub>F</sub>	$    I_F = 20 \text{ A}; \qquad T_{VJ} = 25^{\circ}\text{C} \\     I_F = 20 \text{ A}; \qquad T_{VJ} = 125^{\circ}\text{C} $		1.7 1.2	2.1 V V	
I <sub>R</sub>	$ \begin{array}{ll} V_{\text{R}} = V_{\text{RRM}}; & T_{\text{VJ}} = & 25^{\circ}\text{C} \\ V_{\text{R}} = V_{\text{RRM}}; & T_{\text{VJ}} = & 125^{\circ}\text{C} \end{array} $		40	0.4 mA μA	
l <sub>RM</sub> t <sub>rr</sub>	$\label{eq:linear} \left. \begin{array}{l} I_{F}=5~A; & -di_{F}/dt=150~A/\mu s; \\ V_{R}=150~V; & T_{VJ}=125^{\circ}C \end{array} \right.$		2.1 20	A ns	
C	$V_{R} = 150 \text{ V};  T_{VJ} = 125^{\circ}\text{C}$		16	pF	
R <sub>thJC</sub>				3.5 K/W	

Data according to IEC 60747 and per diode unless otherwise specified

## Features

GaAs Schottky Diode with Enhanced Barrier Height:

- lowest operating forward voltage drop due to additional injection of minority carriers
- high switching speed
- low junction capacity of GaAs diode independent from temperature
- short and low reverse recovery current peak due to short lifetime of minority carriers
- soft turn off
- low leakage current
- ISOPLUS220™ Package:
- isolated back surface
- low coupling capacy between pins and heatsink
- enlarged creepage
- high reliability
- industry standard outline

## Applications

Power Factory Correction (PFC) Switched Mode Power Supplies:

- AC-DC converters
- DC-DC converters *with:*
- With
- high switching frequency
- high efficiency
- low EMI
- for use e.g. in:
- telecomcomputer
- automotive equipment

IXYS reserves the right to change limits, Conditions and dimensions.

0520

## LIXYS

Component					
Symbol	Conditions	Maximum F	Maximum Ratings		
I <sub>RMS</sub>	per pin	45	А		
T <sub>VJ</sub> T <sub>stg</sub>		-55+175 -55+150	O° O°		
VISOL	$I_{ISOL} \le 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~		
F <sub>c</sub>	mounting force with clip	1050	Ν		

Symbol	I Conditions Characteris min.   typ.		stic Values max.	
C <sub>p</sub>	coupling capacity between shorted pins and mounting tab in the case		15	pF
R <sub>thCS</sub>			0.3	K/W
Weight			2	g

